

Description

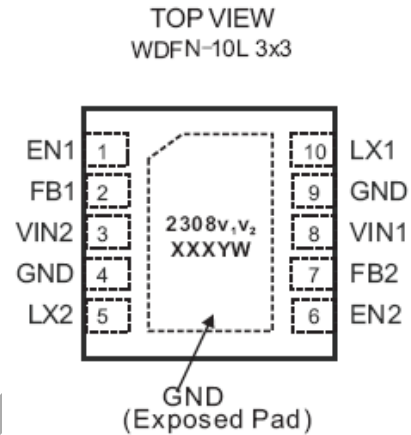
The PAM2308 is a dual step-down current-mode, DC-DC converter. At heavy load, the constant frequency PWM control performs excellent stability and transient response. To ensure the longest battery life in portable applications, the PAM2308 provides a power-saving Pulse-Skipping Modulation (PSM) mode to reduce quiescent current under light load operation.

The PAM2308 supports a range of input voltages from 2.5V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, USB, and other standard power sources. The dual output voltages are available for 3.3V, 2.8V, 2.5V, 1.8V, 1.5V, 1.2V or adjustable. All versions employ internal power switch and synchronous rectifier to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than 0.1µA. Other key features include under-voltage lockout to prevent deep battery discharge.

Features

- Efficiency up to 96%
- Only 40µA (typ per channel) Quiescent Current
- Output Current: Up to 1A per Channel
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency
- Soft-Start
- Under-Voltage Lockout
- Short Circuit Protection
- Thermal Shutdown
- Small WDFN3x3-10L Packages
- Pb-Free Package and RoHS Compliant

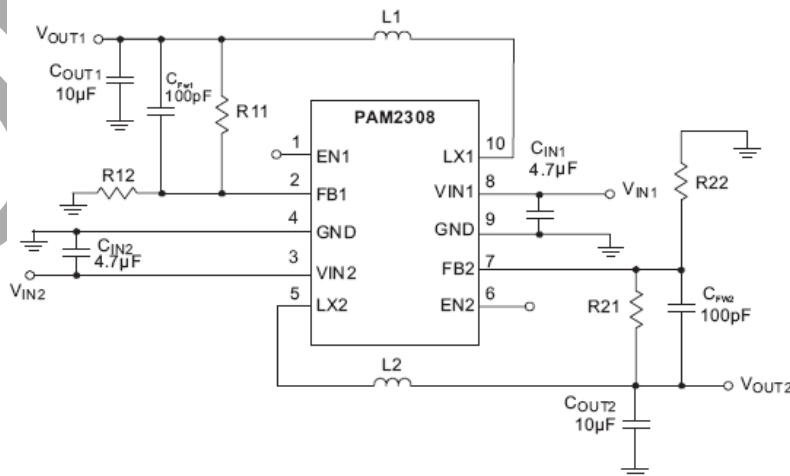
Pin Assignments



Applications

- Cellular Phone
- Portable Electronics
- Personal Information Appliances
- Wireless and DSL Modems
- MP3 Players

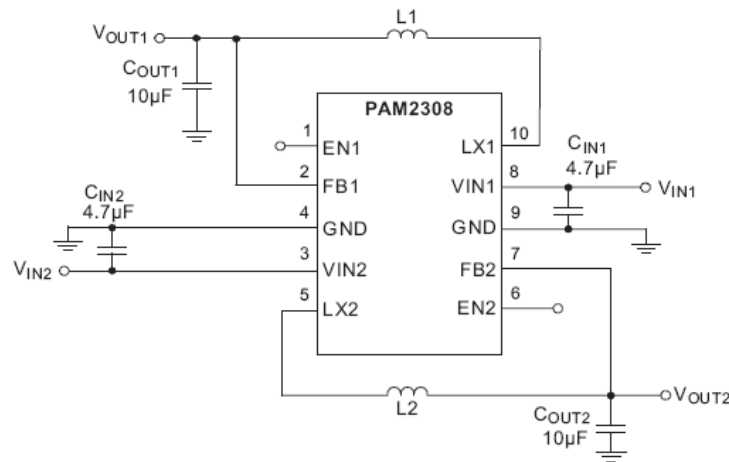
Typical Applications Circuit



$$V_{OUTx} = V_{REF} \left(1 + \frac{R_{x1}}{R_{x2}} \right)$$

Figure 1. Adjustable Voltage Regulator

Typical Applications Circuit (cont.)



$V_{OUTx} = 1.2V, 1.5V, 1.8V, 2.5V, 2.8V$ or $3.3V$
Figure 2. Fixed Voltage Regulator

Pin Descriptions

Pin Name	Pin Number	Function
EN1	1	Chip Enable of Channel 1(Active High). $V_{EN1} \leq V_{IN1}$.
FB1	2	Feedback of Channel 1.
VIN2	3	Power Input of Channel 2.
GND	4, 9	Ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.
LX2	5	Pin for Switching of Channel 2.
EN2	6	Chip Enable of Channel 2 (Active High). $V_{EN2} \leq V_{IN2}$.
FB2	7	Feedback of Channel 2.
VIN1	8	Power Input of Channel 1.
LX1	10	Pin for Switching of Channel 1.

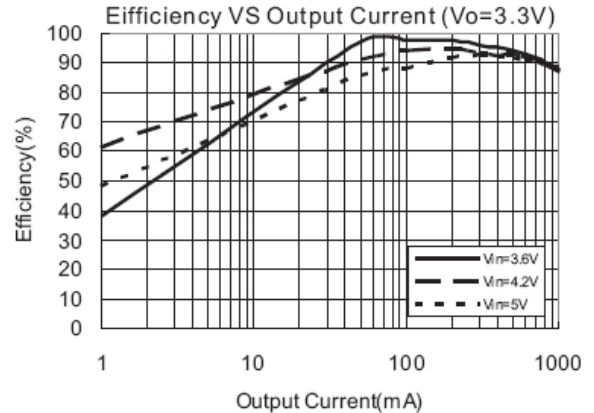
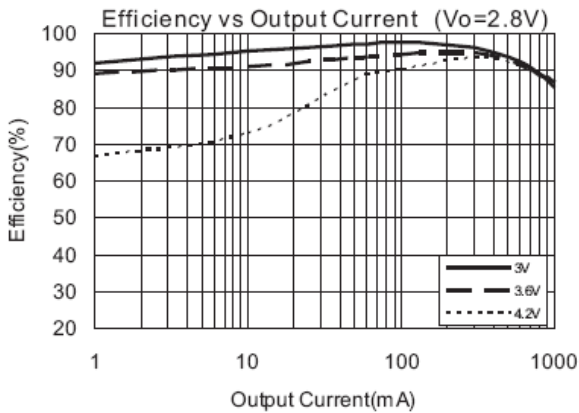
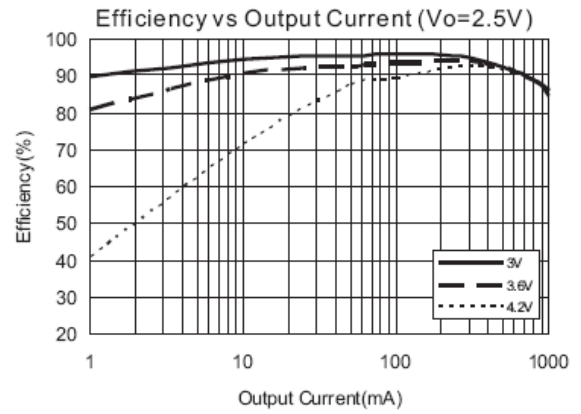
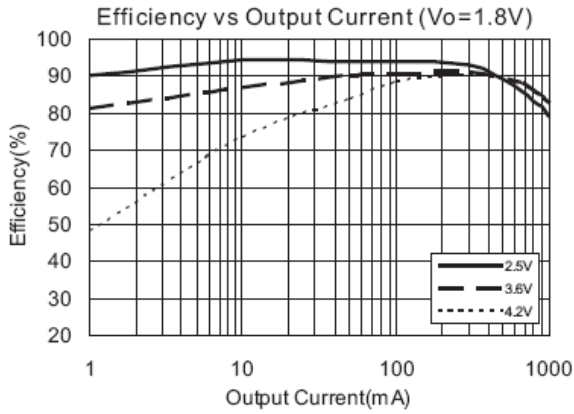
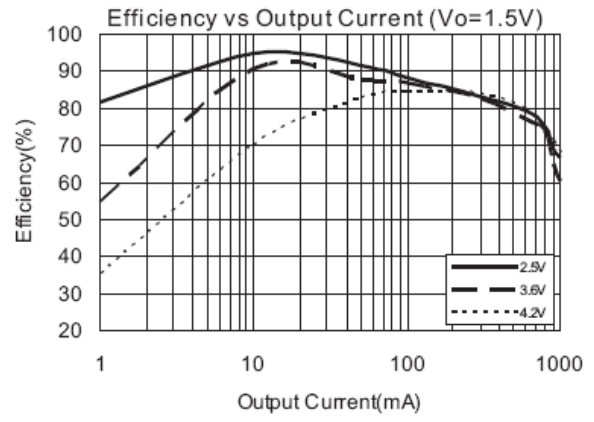
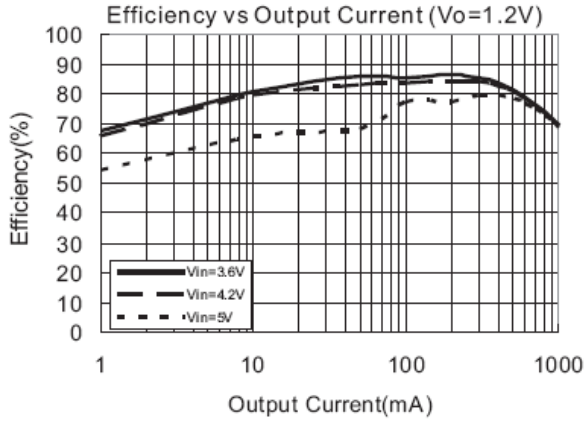
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Electrical Characteristics (@T_A = +25°C, V_{IN} = 3.6V, V_O = 1.8V, C_{IN} = 10μF, C_O = 10μF, L = 2.2μH, unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Input Voltage Range	V _{IN}		2.5		5.5	V
Regulated Feedback Voltage	V _{FB}		0.588	0.6	0.612	V
Reference Voltage Line Regulation	ΔV _{FB}			0.3		%/V
Regulated Output Voltage Accuracy	V _O	I _O = 100mA	-3		+3	%
Peak Inductor Current	I _{PK}	V _{IN} = 3V, V _{FB} = 0.5V or V _O = 90%		1.5		A
Output Voltage Line Regulation	LNR	V _{IN} = 2.5V TO 5V, I _O = 10mA		0.2	0.5	%/V
Output Voltage Load Regulation	LDR	I _O = 1mA to 1A		0.5	1.5	%
Quiescent Current (per channel)	I _Q	No load		40	70	μA
Shutdown Current (per channel)	I _{SD}	V _{EN} = 0V		0.1	1	μA
Oscillator Frequency	f _{osc}	V _O = 100%	1.2	1.5	1.8	MHz
		V _{FB} = 0V or V _O = 0V		500		kHz
Drain-Source On-State Resisistance	R _{DS(ON)}	I _{DS} = 100mA	P MOSFET	0.3	0.45	Ω
			N MOSFET	0.35	0.5	Ω
SW Leakage Current	I _{LSW}			±0.01	1	μA
High Efficiency	η			96		%
EN Threshold High	V _{EH}		1.5			V
EN Threshold Low	V _{EL}				0.3	V
EN Leakage Current	I _{EN}			±0.01		μA
Over Temperature Protection	OTP			150		°C
OTP Hysteresis	OTH			30		°C

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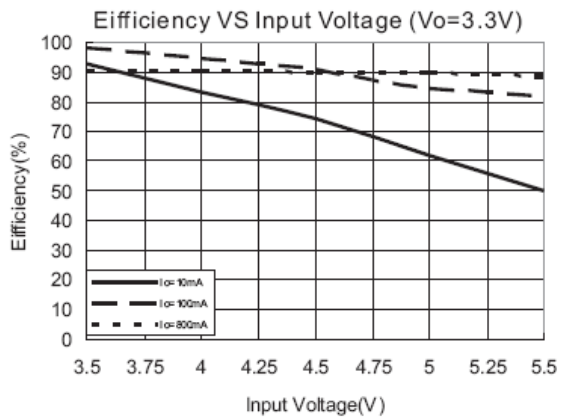
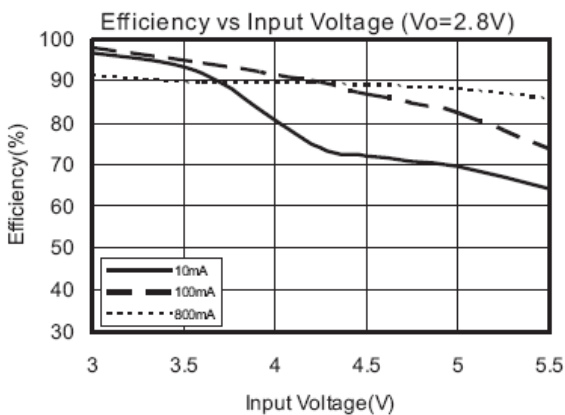
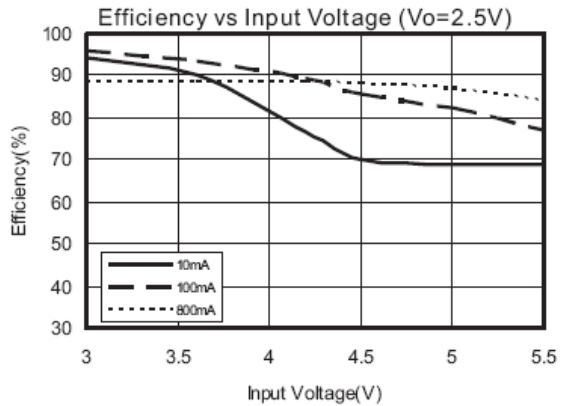
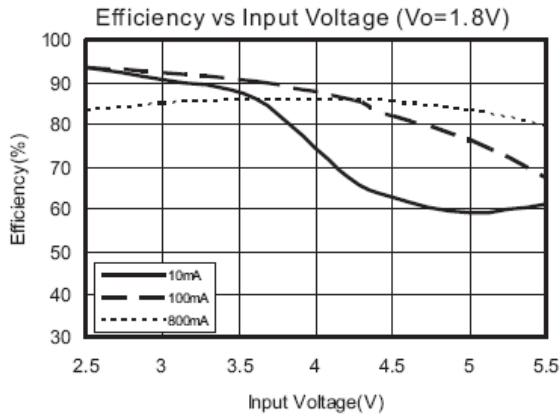
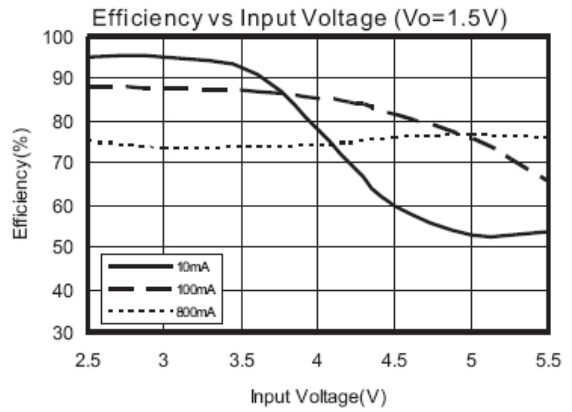
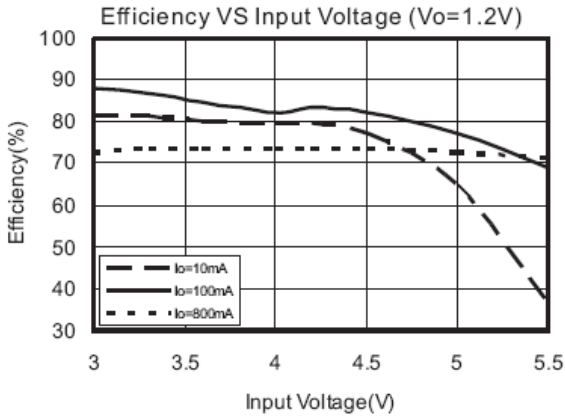
Typical Performance Characteristics (@ $T_A = +25^\circ\text{C}$, $C_{IN} = 10\mu\text{F}$, $C_O = 10\mu\text{F}$, $L = 4.7\mu\text{H}$, unless otherwise specified.)



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Typical Performance Characteristics (cont.)

(@T_A = +25°C, C_{IN} = 10µF, C_O = 10µF, L = 4.7µH, unless otherwise specified.)

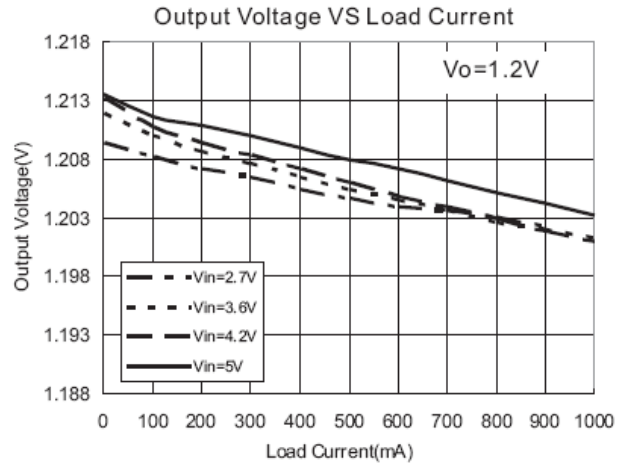
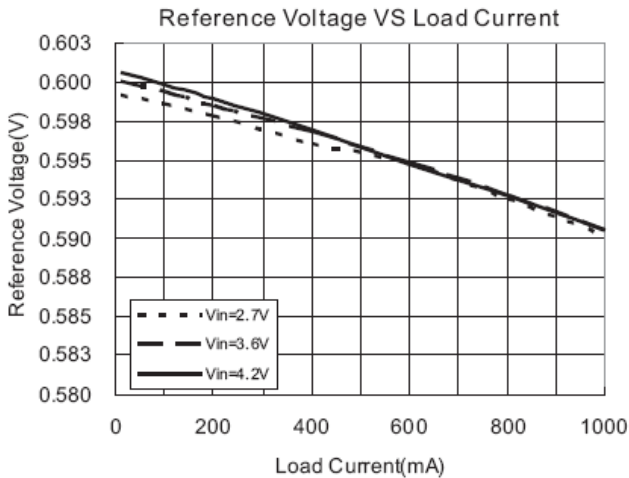
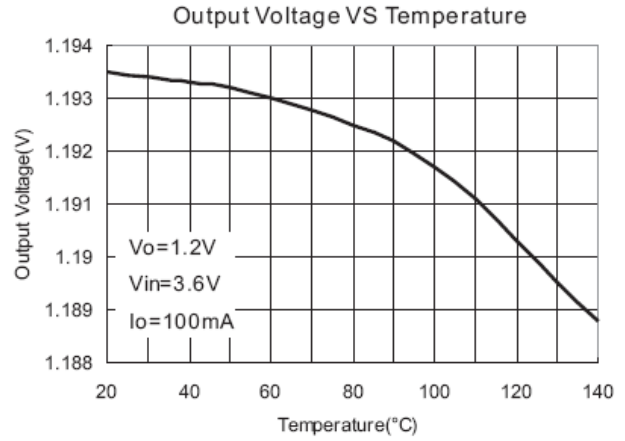
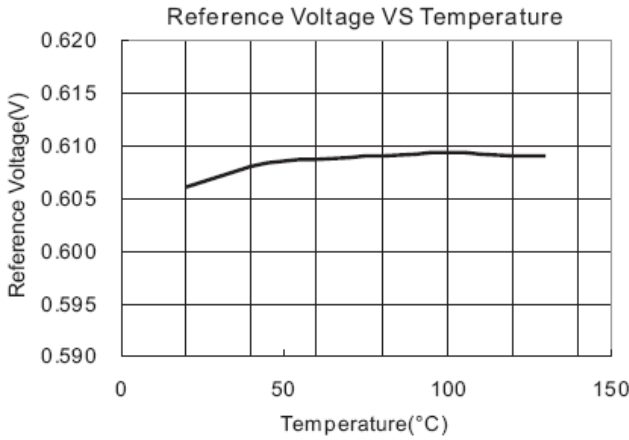
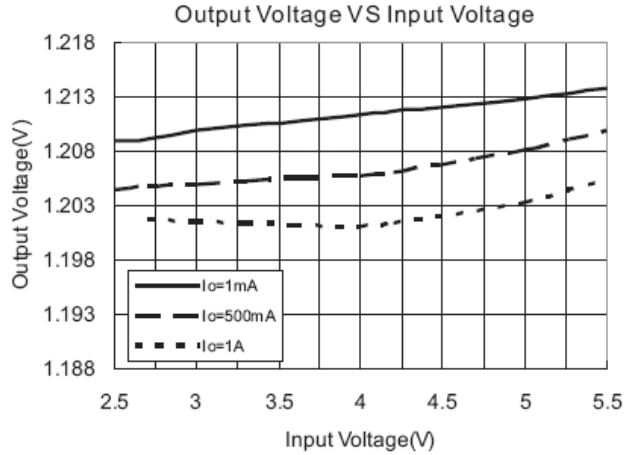
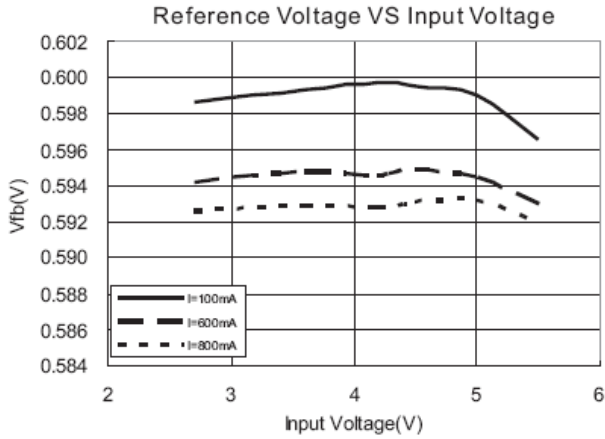


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Typical Performance Characteristics (cont.)

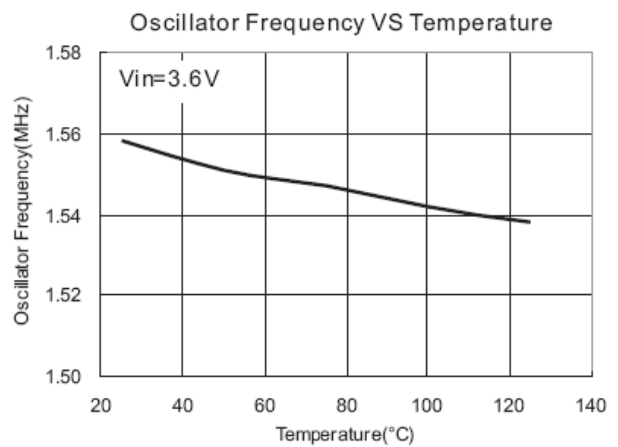
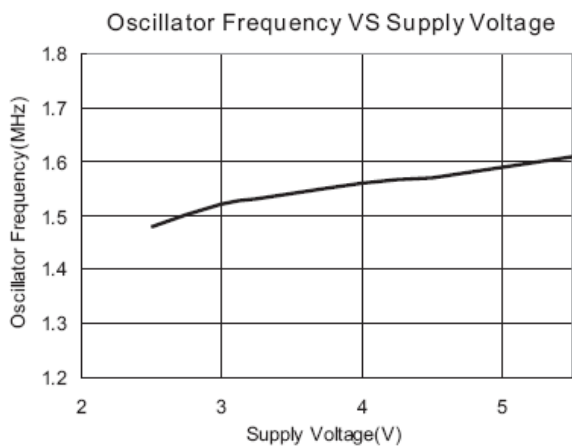
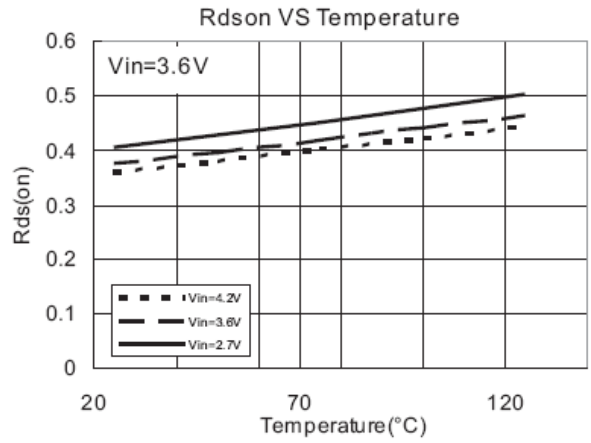
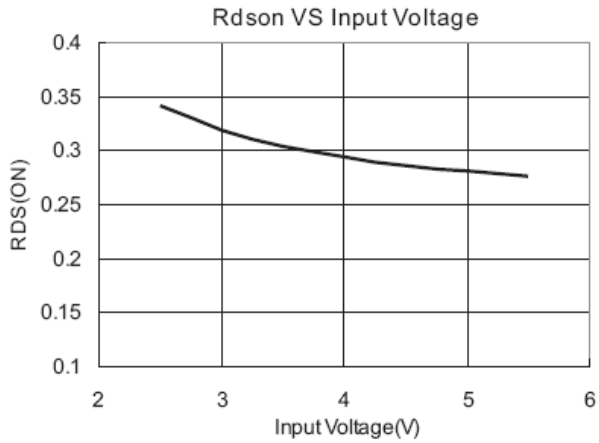
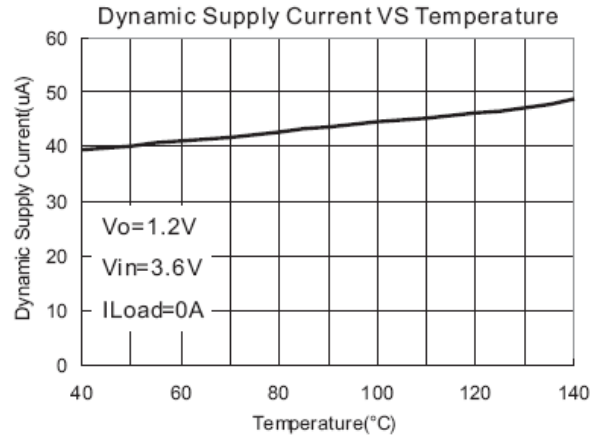
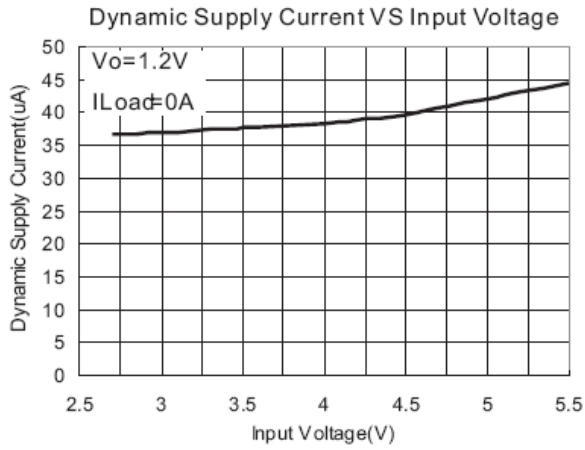
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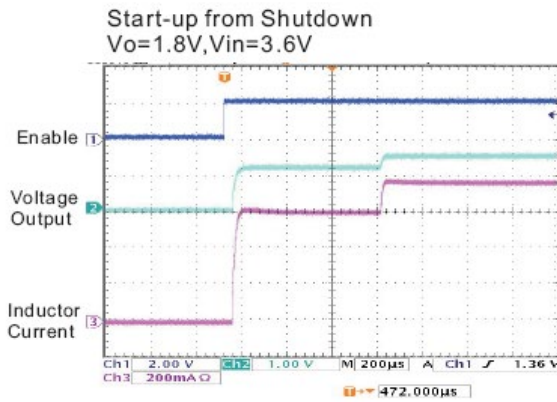
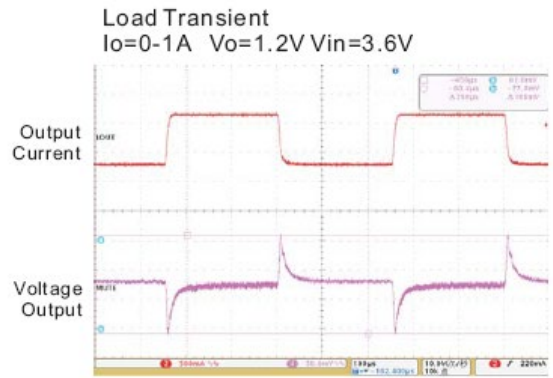
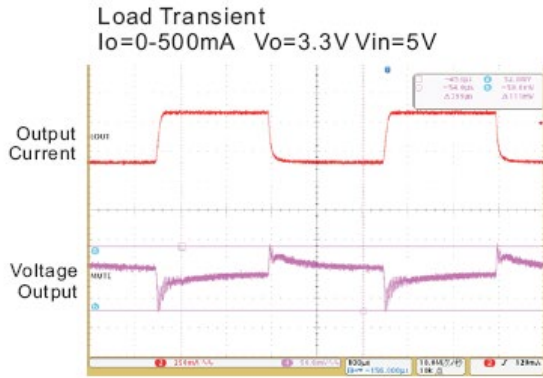
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Typical Performance Characteristics (cont.)

(@T_A = +25°C, C_{IN} = 10µF, C_O = 10µF, L = 4.7µH, unless otherwise specified.)



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Application Information

The basic PAM2308 application circuit is shown on Page 1 and 2. External component selection is determined by the load requirement, selecting L first and then C_{IN} and C_{OUT}.

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1μH to 4.7μH. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V_{IN} or V_{OUT} also increases the ripple current as shown in Equation 1. A reasonable starting point for setting ripple current is ΔI_L = 400mA (40% of 1A).

$$\Delta I_L = \frac{1}{f(L)} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right) \quad \text{Equation (1)}$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.4A rated inductor should be enough for most applications (1A + 400mA). For better efficiency, choose a low DC-resistance inductor.

V _O	1.2V	1.5V	1.8V	2.5V	3.3V
L	2.2μH	2.2μH	2.2μH	4.7μH	4.7μH

C_{IN} and C_{OUT} Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle V_{OUT}/V_{IN}. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN} \text{ required } I_{RMS} \cong I_{OMAX} \frac{[V_{OUT}(V_{IN} - V_{OUT})]^{1/2}}{V_{IN}}$$

This formula has a maximum at V_{IN} = 2V_{OUT}, where I_{RMS} = I_{OUT} / 2. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Consult the manufacturer if there is any question.

The selection of C_{OUT} is driven by the required effective series resistance (ESR).

Typically, once the ESR requirement for C_{OUT} has been met, the RMS current rating generally far exceeds the I_{ripple} (P-P) requirement. The output ripple ΔV_{OUT} is determined by:

$$\Delta V_{OUT} \approx \Delta I_L \left(ESR + \frac{1}{8fC_{OUT}} \right)$$

Where f = operating frequency, C_{OUT} = output capacitance and ΔI_L = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since ΔI_L increases with input voltage.

Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

Thermal Consideration

Thermal protection limits power dissipation in the PAM2308. When the junction temperature exceeds +150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below +120°C.

For continuous operation, the junction temperature should be maintained below 125°C. The power dissipation is defined as:

$$P_D = I_o^2 \frac{V_o R_{DS(ON)H} + (V_{IN} - V_o) R_{DS(ON)L}}{V_{IN}} + (t_{sw} F_s I_o + I_Q) V_{IN}$$

I_Q is the step-down converter quiescent current. The term t_{sw} is used to estimate the full load step-down converter switching losses.

Application Information (cont.)

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_D = I_O^2 R_{DS(ON)H} + I_Q V_{IN}$$

Since $R_{DS(ON)}$, quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where $T_{J(MAX)}$ is the maximum allowable junction temperature +125°C. T_A is the ambient temperature and θ_{JA} is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance θ_{JA} of W-DFN3X3 is 60°C/W. The maximum power dissipation at $T_A = +25^\circ\text{C}$ can be calculated by following formula:

$$P = (125^\circ\text{C} - 25^\circ\text{C}) / 60^\circ\text{C/W} = 1.66\text{W}$$

Setting the Output Voltage

The internal reference is 0.6V (Typical). The output voltage is calculated as below:

$$V_O = 0.6 \times \left(1 + \frac{R_1}{R_2} \right)$$

The output voltage is given by Table 1.

Table 1: Resistor selection for output voltage setting.

V _o	R1	R2
1.2V	100k	100k
1.5V	150k	100k
1.8V	200k	100k
2.5V	380k	120k
3.3V	540k	120k

100% Duty Cycle Operation

As the input voltage approaches the output voltage, the converter turns the P-Channel transistor continuously on. In this mode the output voltage is equal to the input voltage minus the voltage drop across the P-Channel transistor:

$$V_{OUT} = V_{IN} - I_{LOAD} (R_{DS(ON)} + R_L)$$

where $R_{DS(ON)}$ = P-Channel switch ON resistance, I_{LOAD} = Output Current, R_L = Inductor DC Resistance

UVLO and Soft-Start

The reference and the circuit remain reset until the V_{IN} crosses its UVLO threshold.

The PAM2308 has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates the output voltage overshoot. The soft-start acts as a digital circuit to increase the switch current in several steps to the P-Channel current limit (1500mA).

Short Circuit Protection

The switch peak current is limited cycle-by-cycle to a typical value of 1500mA. In the event of an output voltage short circuit, the device operates with a frequency of 400kHz and minimum duty cycle, therefore the average input current is typically 200mA.

Thermal Shutdown

When the die temperature exceeds +150°C, a reset occurs and the reset remains until the temperature decrease to +120°C, at which time the circuit can be restarted.

Application Information (cont.)

PCB Layout Check List

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the PAM2308. These items are also illustrated graphically in Figure 1. Check the following in your layout:

1. The power traces, consisting of the GND trace, the SW trace and the V_{IN} trace should be kept short, direct and wide.
2. Does the FB pin connect directly to the feedback resistors? The resistive divider R1/R2 must be connected between the (+) plate of C_{OUT} and ground.
3. Does the (+) plate of C_{IN} connect to V_{IN} as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
4. Keep the switching node, SW, away from the sensitive FB node.
5. Keep the (-) plates of C_{IN} and C_{OUT} as close as possible.

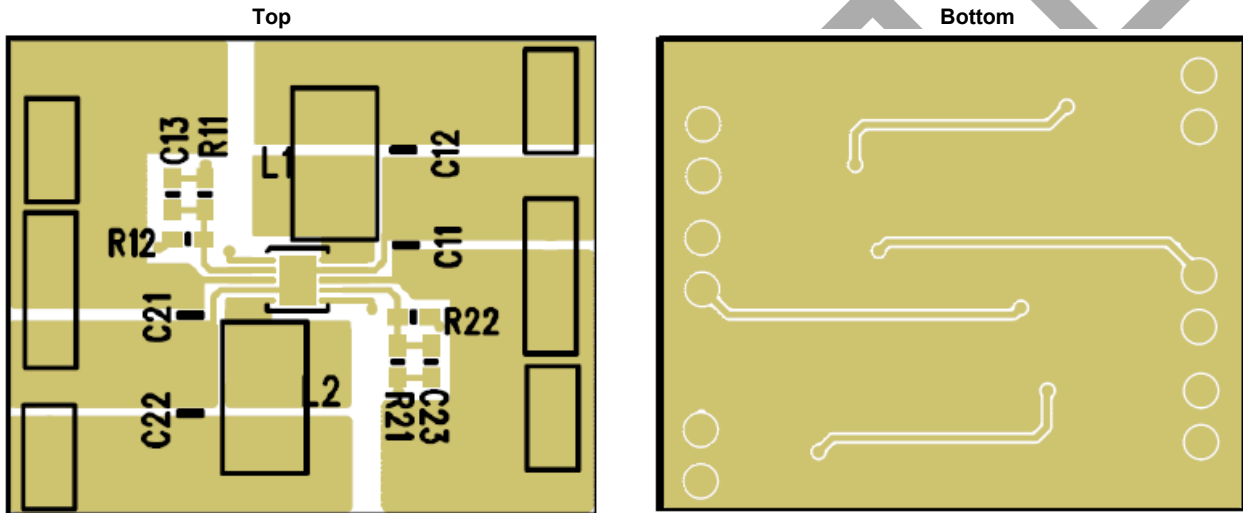
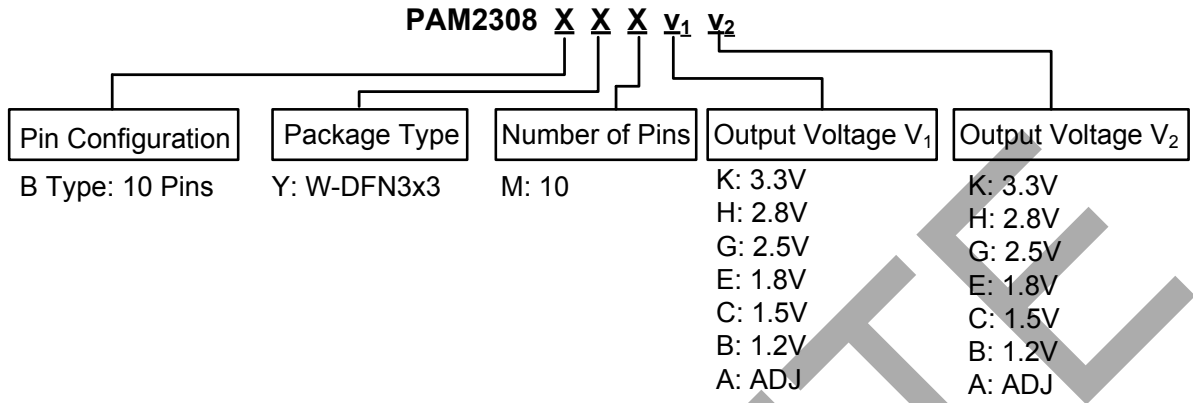


Figure 1. PAM2308 Suggested Layout

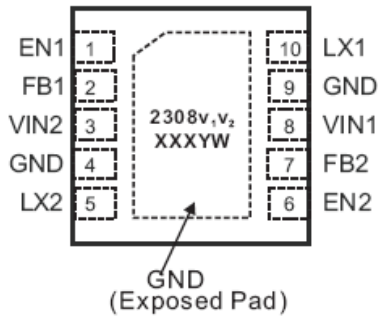
Ordering Information



Part Number	Part Marking	Package Type	Standard Package
PAM2308BYMv ₁ v ₂	2308v ₁ v ₂ XXXYW	W-DFN3x3-10	3000 Units/Tape & Reel

Marking Information

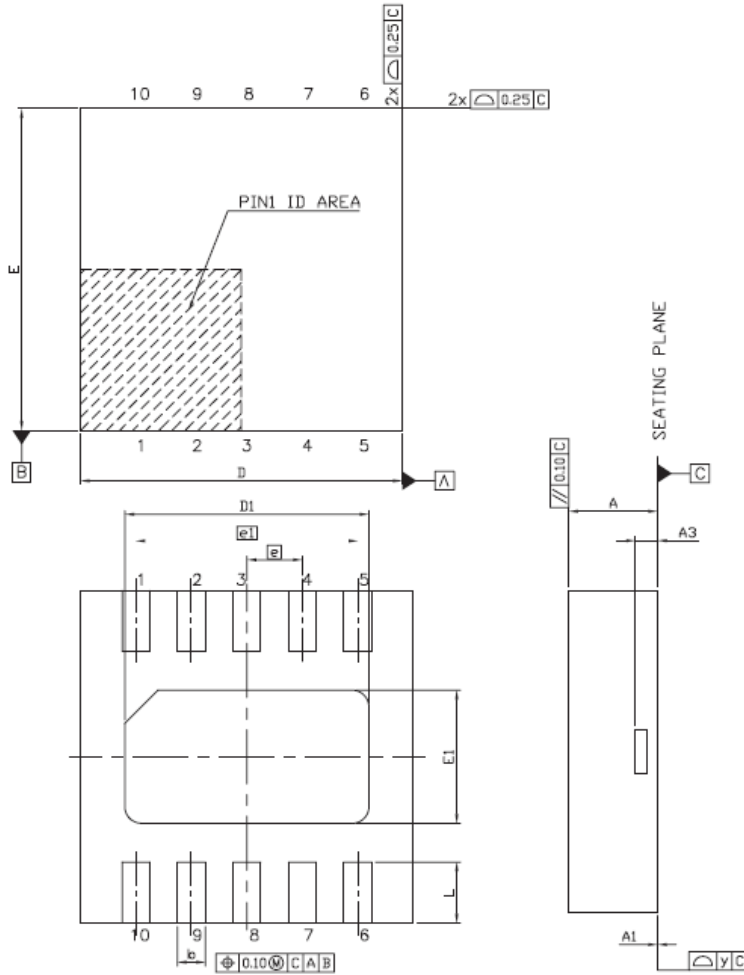
TOP VIEW
WDFN-10L 3x3



- v₁: Output Voltage 1
- v₂: Output Voltage 2
(refer to "Ordering Information")
- X: Internal Code
- Y: Year
- W: Week

Package Outline Dimensions (All dimensions in mm.)

W-DFN3x3-10



SYMBOL	DIMENSION (MM)		
	MIN	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A3	0.203 REF		
b	0.18	0.25	0.30
D	2.90	3.00	3.10
D1	2.10	2.20	2.30
E	2.90	3.00	3.10
E1	1.10	1.20	1.30
L	0.45	0.55	0.65
e	0.50 BASIC		
e1	2.00 BASIC		
y	0		0.08

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